



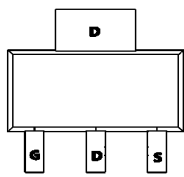
TM10P10SI

P-Channel Enhancement Mosfet

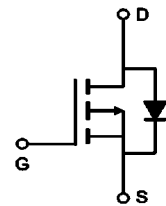
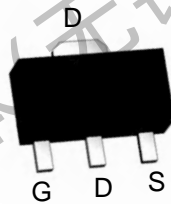
<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = -100V$ $I_D = -10A$ $R_{DS(ON)} = 185m\Omega (typ.) @ V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p>
--	---



SI:SOT-89-3L



Marking: 10P10



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)				
Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-100	V	
V_{GS}	Gate-Source Voltage	± 20	V	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-10	A	
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	4	A	
I_{DM}	Pulsed Drain Current	-20	A	
EAS	Single Pulse Avalanche Energy	---	mJ	
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	2.4	W	
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$	
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$	

Thermal Data				
Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	69.4	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	8	$^\circ C/W$

TM10P10SI

P-Channel Enhancement Mosfet

P-Channel Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-3A$	---	185	240	m Ω
		$V_{GS}=-4.5V, I_D=-2A$	---	208	270	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1	-2	-3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V, T_J=25^\circ C$	---	---	-1	μA
		$V_{DS}=-100V, V_{GS}=0V, T_J=85^\circ C$	---	---	-30	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	---	---	Ω
Q_g	Total Gate Charge (-10V)	$V_{DS}=-50V, V_{GS}=-10V, I_D=-2A$	---	29	---	nC
Q_{gs}	Gate-Source Charge		---	2.9	---	
Q_{gd}	Gate-Drain Charge		---	5.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-50V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-2A$	---	9.6	---	ns
T_r	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	60	---	
T_f	Fall Time		---	36	---	
C_{iss}	Input Capacitance	$V_{DS}=-50V, V_{GS}=0V, f=1MHz$	---	1290	---	μF
C_{oss}	Output Capacitance		---	34	---	
C_{rss}	Reverse Transfer Capacitance		---	28	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	10	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	-1.2	V

TM10P10SI

P-Channel Enhancement Mosfet

Typical Characteristics

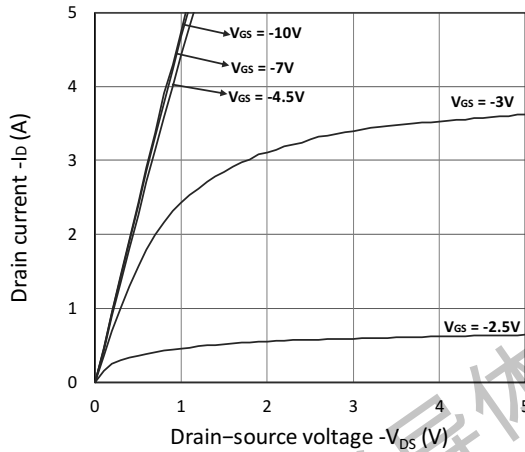


Figure 1. Output Characteristics

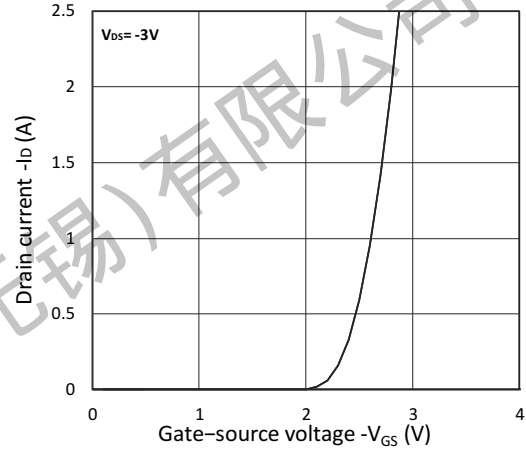


Figure 2. Transfer Characteristics

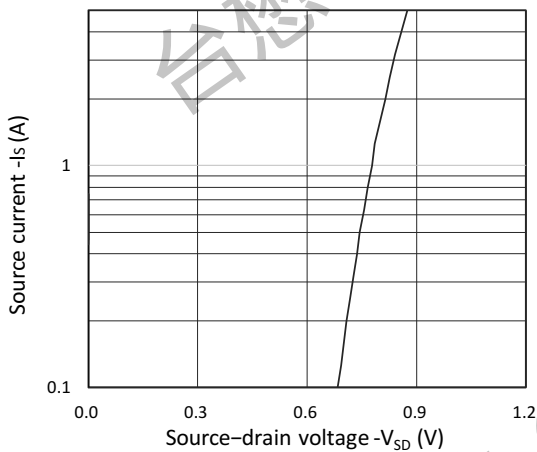


Figure 3. Forward Characteristics of Reverse

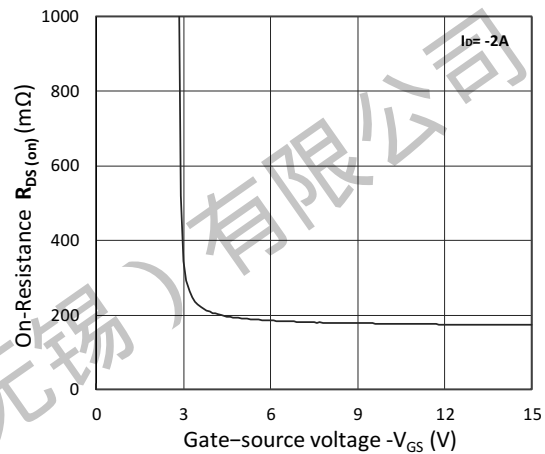


Figure 4. $R_{DS(on)}$ vs. V_{GS}

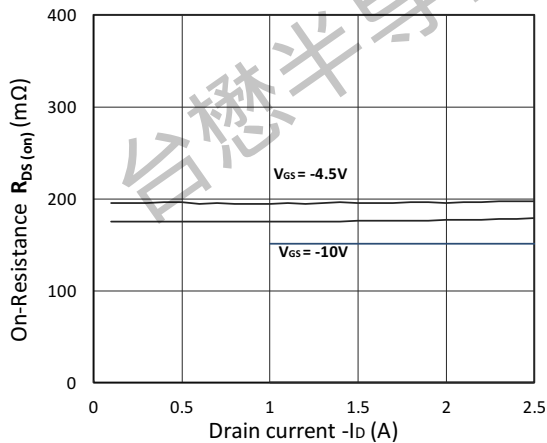


Figure 5. $R_{DS(on)}$ vs. I_D

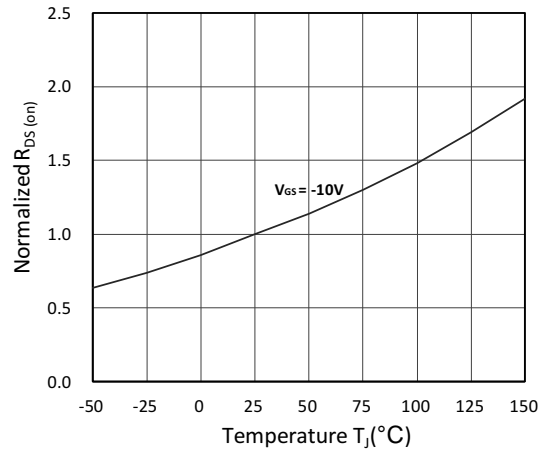


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

TM10P10SI

P-Channel Enhancement Mosfet

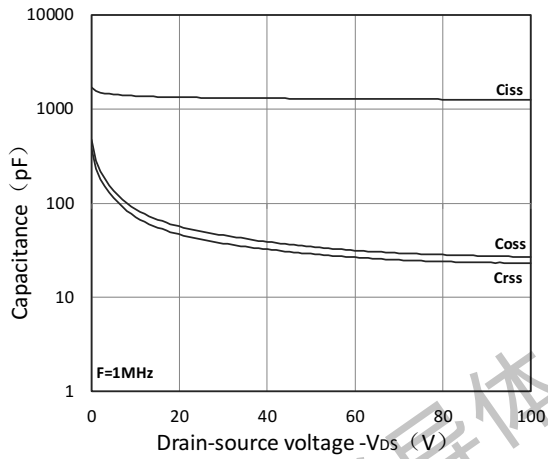


Figure 7. Capacitance Characteristics

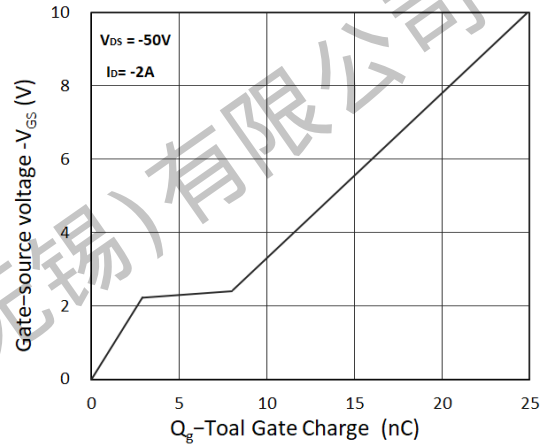


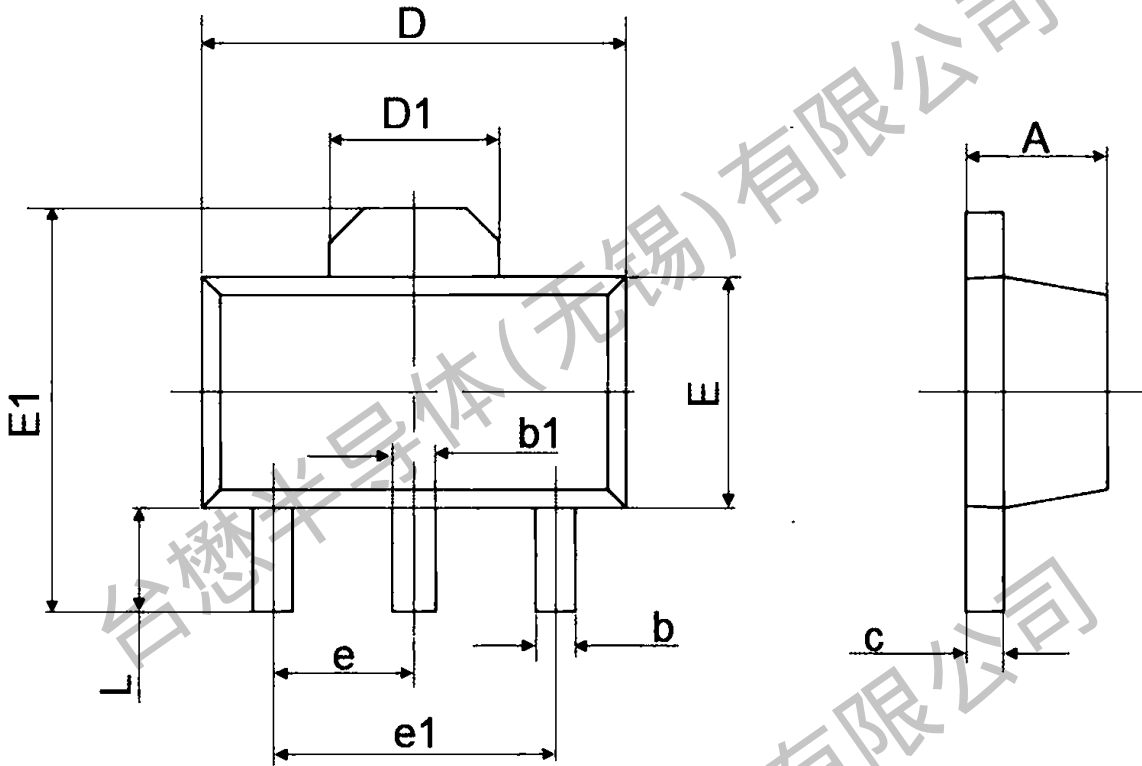
Figure 8. Gate Charge Characteristics



TM10P10SI

P-Channel Enhancement Mosfet

Package Mechanical Data:SOT-89-3L

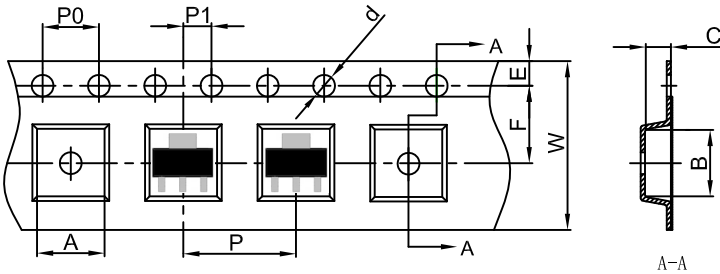


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

TM10P10SI

P-Channel Enhancement Mosfet

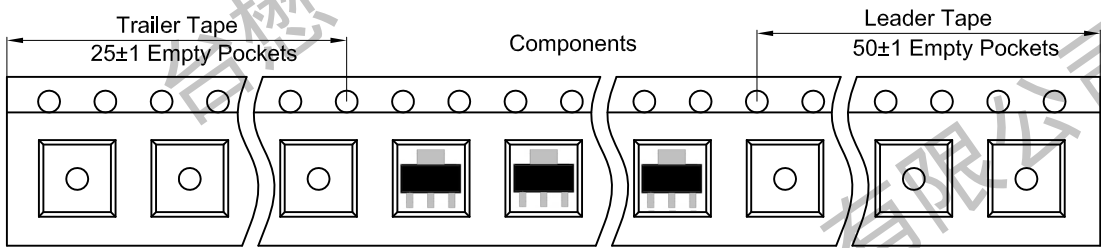
SOT-89-3L Embossed Carrier Tape



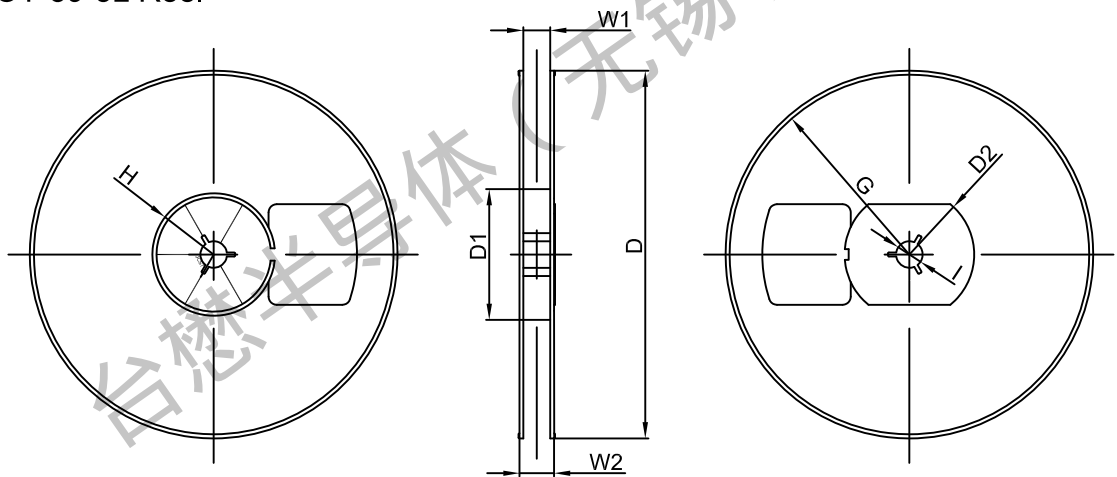
Packaging Description:
SOT-89-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 1,000 units per 7" or 18.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-89-3L	4.85	4.45	1.85	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOT-89-3L Tape Leader and Trailer



SOT-89-3L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	R32.00	R86.50	R30.00	Ø13.00	13.20	16.50

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
1000 pcs	7 inch	10,000 pcs	205x195x220	40,000 pcs	430x415x240	



Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.09.19	23.09	Original	